

Medium current, high performance, low voltage PNP transistor

Features

- Very low collector to emitter saturation voltage
- DC current gain, h_{FE} >100
- 3 A continuous collector current
- 40 V breakdown voltage V_{(BR)CER}
- SOT-223 plastic package for surface mounting circuits in tape and reel packing

Applications

- Power management in portable equipment
- Voltage regulation in bias supply circuits
- Switching regulator in battery charger applications
- Heavy load driver

Description

The device in manufactured in low voltage PNP planar technology by using a "Base Island" layout. The resulting transistor shows exceptional high gain performance coupled with very low saturation voltage.

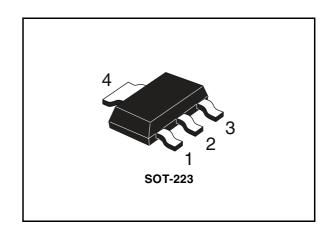


Figure 1. Internal schematic diagram

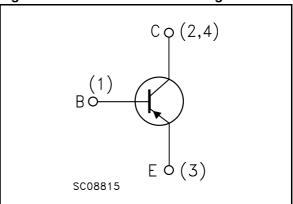


Table 1. Device summary

Order code	Marking	Package	Packaging
STN790A	N790A	SOT-223	Tape and reel

Electrical ratings STN790A

1 Electrical ratings

Table 2. Absolute maximum rating

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-base voltage (I _E = 0)	-40	V
V _{CER}	Collector-emitter voltage ($R_{BE} = 47 \Omega$)	-40	V
V _{CEO}	Collector-emitter voltage (I _B = 0)	-30	V
V _{EBO}	Emitter-base voltage (I _C = 0)	-5	V
I _C	Collector current	-3	Α
I _{CM}	Collector peak current (t _P < 5 ms)	-6	Α
P _{tot}	Total dissipation at T _{amb} = 25 °C	1.6	W
T _{stg}	Storage temperature	-65 to 150	°C
TJ	Max. operating junction temperature	150	°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thj-amb}	Thermal resistance junction-ambient (1) max	78	°C/W

^{1.} Device mounted on PCB area of 1 $\overline{\text{cm}^2}$.

2 Electrical characteristics

 $(T_{case} = 25 \, ^{\circ}C \text{ unless otherwise specified})$

Table 4. Electrical characteristics

Symbol	Parameter	Test cor	nditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector cut-off current (I _E = 0)	$V_{CB} = -30 \text{ V}$ $V_{CB} = -30 \text{ V}$;	T _C = 100 °C			-10 -100	μ Α μ Α
I _{EBO}	Emitter cut-off current (I _C = 0)	V _{EB} = -4 V				-10	μΑ
V _{(BR)CEO} (1)	Collector-emitter breakdown voltage (I _B = 0)			-30			<
V _{(BR)CER} (1)	Collector-emitter breakdown voltage (R _{BE} = 47 Ω)	I _C = -10 mA		-40			V
V _{(BR)CBO}	Collector-base breakdown voltage (I _E = 0)	I _C = -100 μA		-40			V
V _{(BR)EBO}	Emitter-base breakdown voltage (I _C = 0)	I _E = -100 μA		-5			V
	Collector-emitter saturation voltage	I _C = -0.5 A	I _B = -5 mA			-0.15	٧
		I _C = -1.2 A	$I_B = -20 \text{ mA}$			-0.25	V
V _{CE(sat)} (1)		I _C = -2 A	$I_B = -20 \text{ mA}$			-0.5	V
, ,		I _C = -3 A	$I_B = -100 \text{ mA}$			-0.7	V
		•	$I_B = -100 \text{ mA}$				
		T _J = 100 °C				-0.9	V
V _{BE(sat)} (1)	Base-emitter saturation voltage	I _C = -1 A	I _B = -10 mA		-0.8	-1	V
V _{BE(on)} (1)	Base-emitter on voltage	I _C = -1 A	$V_{CE} = -2 V$		-0.8	-1	٧
		I _C = -10 mA	V _{CE} = -2 V	100	200	400	
h _{FE} ⁽¹⁾	DC current gain	I _C = -500 mA	V _{CE} = -2 V	100	200	400	
		I _C = -1 A	$V_{CE} = -2 V$	100			
		I _C = -2 A	$V_{CE} = -1 V$	100	160		
		I _C = -3 A	$V_{CE} = -1 V$	90	130		

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Electrical characteristics STN790A

Table 4.	Electrical characteristics (continued)				
Symbol	Parameter	Test conditions	Min.		

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
f _t	Transition frequency	$I_C = -50 \text{ mA}$ $V_{CE} = -5 \text{ V}$ f = 50 MHz		100		MHz
	Resistive load					
t _d	Delay time	$I_C = -3 \text{ A}$ $V_{CC} = -20 \text{ V}$		180	220	ns
t _r	Rise time	$I_C = -3 \text{ A}$ $V_{CC} = -20 \text{ V}$ $I_{B1} = -I_{B2} = -60 \text{ mA}$		160	210	ns
t _s	Storage time	see Figure 8		250	300	ns
t _f	Fall time			80	100	ns

^{1.} Pulse duration = 300 µs, duty cycle ≤1.5%

2.1 **Electrical characteristics (curves)**

Figure 2. DC current gain

Figure 3. DC current gain

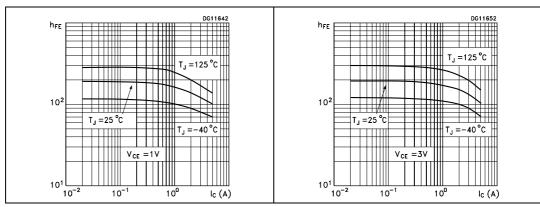
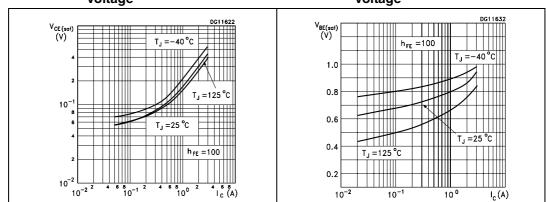


Figure 5. Figure 4. **Collector-emitter saturation Base-emitter saturation** voltage voltage



I_C(A)

DG11670 DG11680 t (n s) t(ns) $V_{CC} = 20 \text{ V}$ $V_{CC} = 20 \text{ V}$ t_d $h_{FE} = 50$ $t_p = 40 \mu s$ $h_{FE} = 50$ $t_p = 40 \mu s$ 500 500 400 400 t_s 300 300 200 200 t, 100 100

0

0.5

1.5 2.0

I_C(A)

Figure 6. Switching time resistive load Figure 7. Switching time resistive load

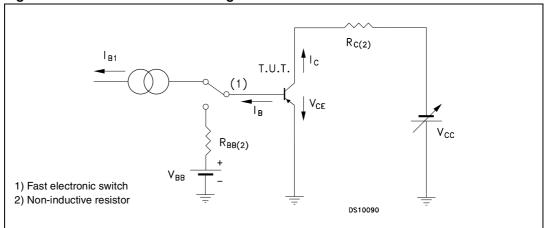
2.2 Test circuit

0

0.5

Figure 8. Resistive load switching test circuit

1.5 2.0

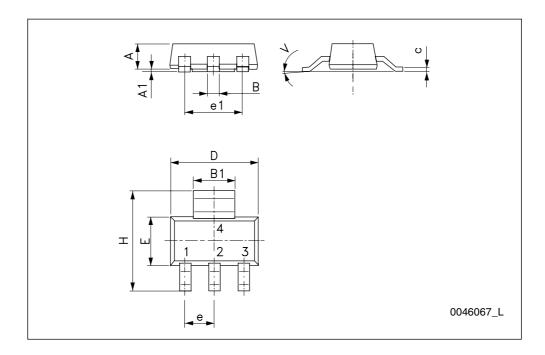


3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

SOT-223 mechanical data

DIM	mm.				
DIM.	min.	typ	max.		
Α			1.80		
A1	0.02		0.1		
В	0.60	0.70	0.85		
B1	2.90	3.00	3.15		
С	0.24	0.26	0.35		
D	6.30	6.50	6.70		
е		2.30			
e1		4.60			
E	3.30	3.50	3.70		
Н	6.70	7.00	7.30		
V			10 °		



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Revision history STN790A

4 Revision history

Table 5. Document revision history

Date	Revision	Changes
24-Mar-2006	3	Updated to new template
26-Jun-2008	4	Updated SOT-223 mechanical data.

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